



Attorney's Docket No.: 10559-587001  
Intel Docket No.: P12768

2812

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Been-Yih Jin, et al. Art Unit : 2812  
Serial No. : 10/081,992 Examiner : Ron E. Pompey  
Filed : February 21, 2002 Assignee : Intel Corporation  
Title : NON-SILICON SEMICONDUCTOR AND HIGH-K GATE DIELECTRIC  
METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Mail Stop Non-Fee Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

AMENDMENT IN REPLY TO OFFICE ACTION OF DECEMBER 24, 2003

Please amend the above-identified application as follows:

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date of Deposit

2/26/01

Signature

Jill Borkman

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